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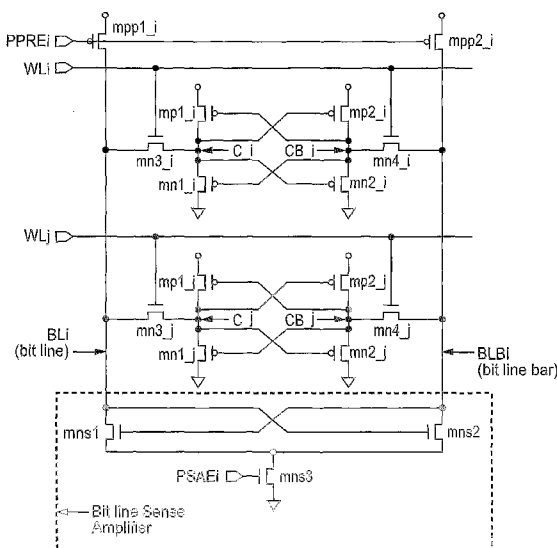
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(54) Title: SRAM CELL STRUCTURE AND CIRCUITS



(57) **Abstract:** An SRAM circuit structure and method for reducing leakage currents and/or increasing the speed of the devices. Various forms of SRAM devices may be fabricated utilizing the techniques, such as single port and dual port RAM devices. By way of example the SRAM structure utilizes separate write and read lines, splits the circuit into portions which can benefit from having differing threshold levels, and can allow splitting read path transistors for connection to a first terminal and a virtual node connected to a source transistor. The structure is particularly well suited for forming transistors in a combination of NMOS and PMOS, or solely in NMOS. Memory arrays may be organized according to the invention in a number of different distributed or lumped arrangements with the reference read paths and sense blocks being either shared or dedicated.

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